

### 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Extended temperature range T<sub>i</sub> = 175 °C
- · Side wettable flanks for optical solder inspection
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Trench MOSFET technology
- AEC-Q101 qualified

### 3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	40	V
V <sub>GS</sub>	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 25 °C		-	-	19	А
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C		-	-	15	W
Static chara	cteristics		- I				
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 8 A; T <sub>j</sub> = 25 °C		-	16.8	20	mΩ

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# 5. Pinning information

Table 2.	Pinning info	rmation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain		
2	D	drain		
3	G	gate		D
4	S	source		
5	D	drain	3 8 4	G-UF 4
6	D	drain	Transparent top view	mbb076 S
7	D	drain	DFN2020MD-6 (SOT1220)	
8	S	source		

# 6. Ordering information

#### Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK6D20-40E		plastic, leadless thermal enhanced ultra thin small outline package with side-wettable flanks (SWF); 6 terminals; 0.65 mm pitch; 2 mm x 2 mm x 0.65 mm body	SOT1220		

## 7. Marking

#### Table 4. Marking codes

Type number	Marking code
BUK6D20-40E	ТА

40 V, N-channel Trench MOSFET

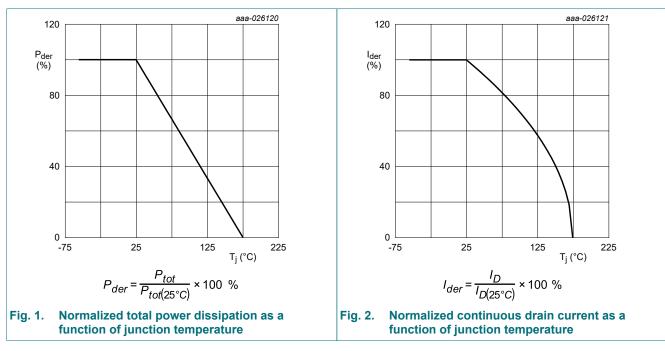
### 8. Limiting values

#### Table 5. Limiting values

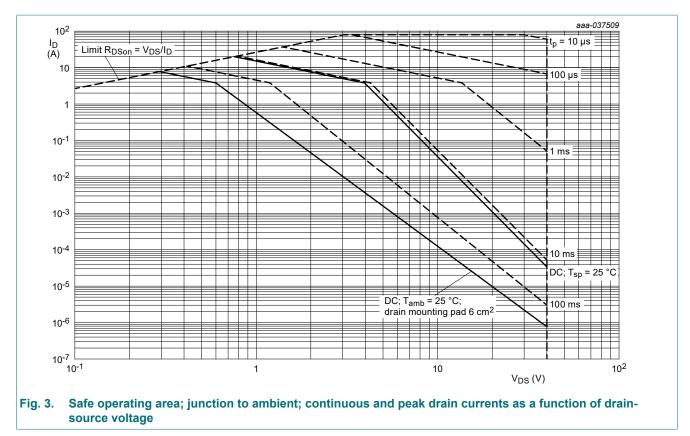
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	40	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 25 °C		-	19	А
		V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 100 °C		-	12	А
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	8	А
I <sub>DM</sub>	peak drain current	$T_{sp}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	80	А
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C		-	15	W
		T <sub>amb</sub> = 25 °C	[1]	-	2.3	W
Tj	junction temperature			-55	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C
Source-drain	n diode					
ls	source current	T <sub>sp</sub> = 25 °C		-	15	А
		T <sub>amb</sub> = 25 °C	[1]	-	2.3	А
I <sub>SM</sub>	peak source current	single pulse; $t_p \le 10 \ \mu s$ ; $T_{sp} = 25 \ ^{\circ}C$		-	61	А
ESD maximu	um rating					
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[2]	-	500	V
Avalanche ru	uggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 1.35 A; DUT in v avalanche (unclamped)		-	28.4	mJ
	L	1		I		

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>. [1] [2] Measured between all pins.



#### 40 V, N-channel Trench MOSFET



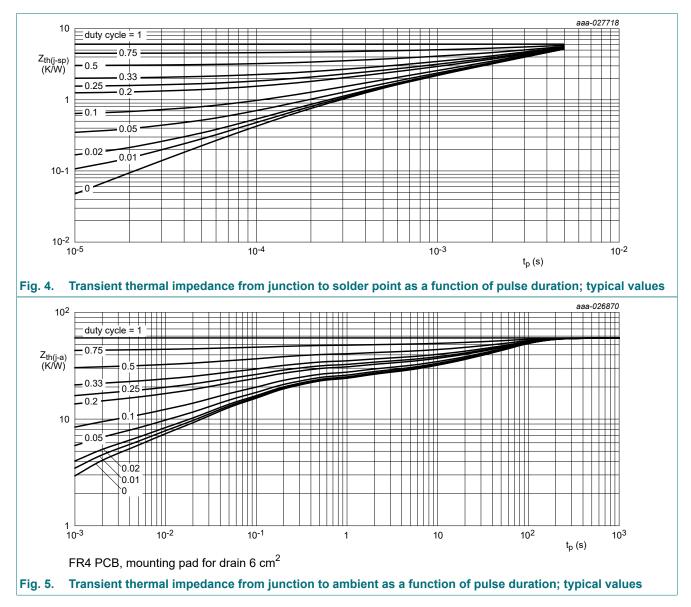
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### 9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	57	66	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	6	10	K/W

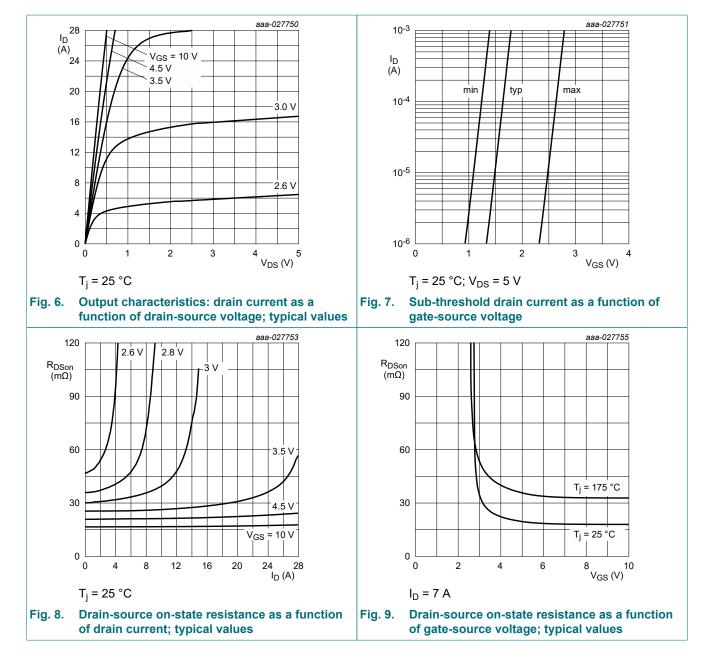
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



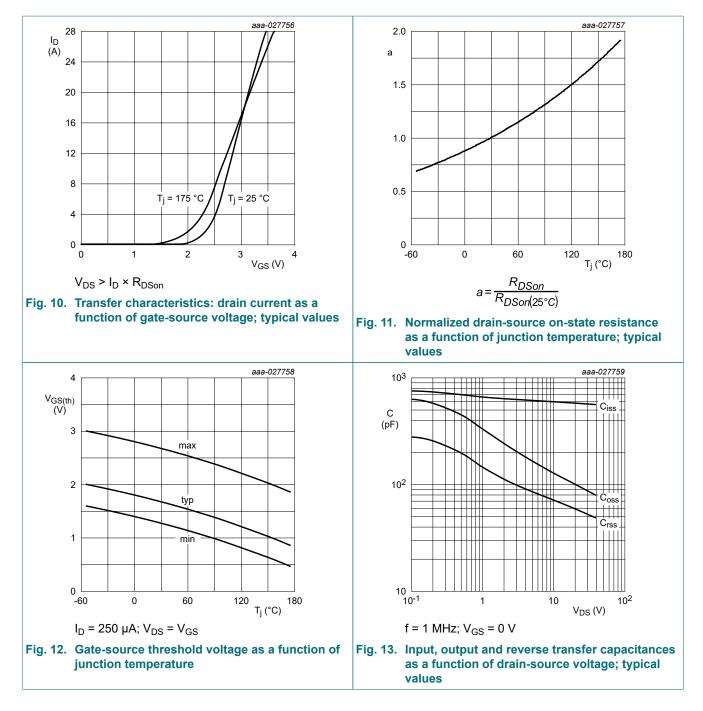
## **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	40	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	I <sub>D</sub> = 250 μA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C	1.3	1.7	2.7	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 8 A; T <sub>j</sub> = 25 °C	-	16.8	20	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 8 A; T <sub>j</sub> = 175 °C	-	32	38	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 6.3 A; T <sub>j</sub> = 25 °C	-	22	30	mΩ
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 7 A; T <sub>j</sub> = 25 °C	-	33	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz	-	1.8	-	Ω
Dynamic ch	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 20 V; I <sub>D</sub> = 7 A; V <sub>GS</sub> = 10 V;	-	11	19	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	2	-	nC
Q <sub>GD</sub>	gate-drain charge		-	2.4	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 20 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	582	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	101	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	58	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 20 V; $I_D$ = 7 A; $V_{GS}$ = 10 V;	-	2	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	5	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	12	-	ns
t <sub>f</sub>	fall time		-	5	-	ns
Source-drai	n diode					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 2.3 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 2.3 A; dI <sub>S</sub> /dt = -100 A/μs;	-	12.8	-	ns
Q <sub>r</sub>	recovered charge	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 20 V; T <sub>j</sub> = 25 °C	-	5.4	-	nC

#### 40 V, N-channel Trench MOSFET

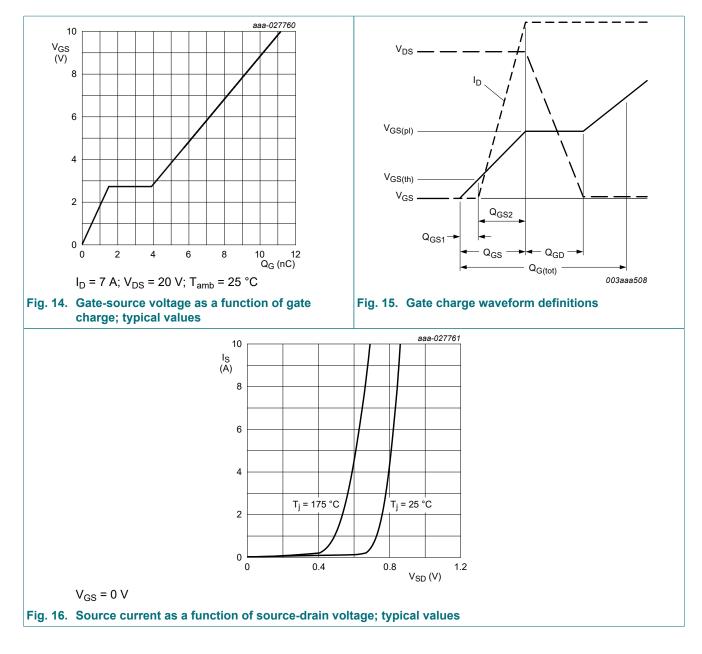


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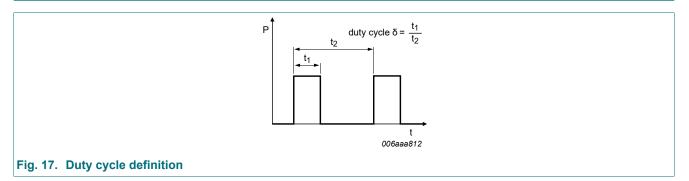
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### **11. Test information**

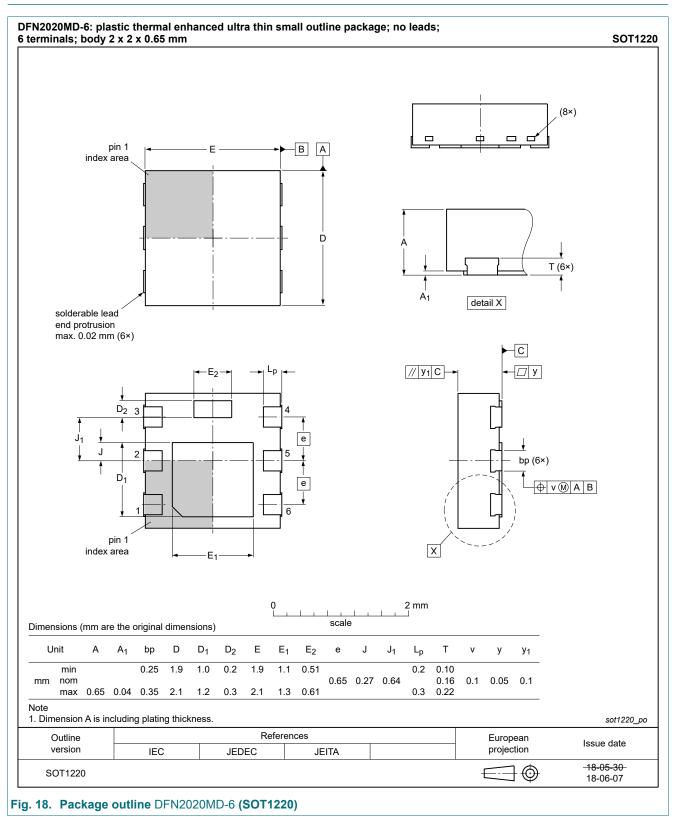


#### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

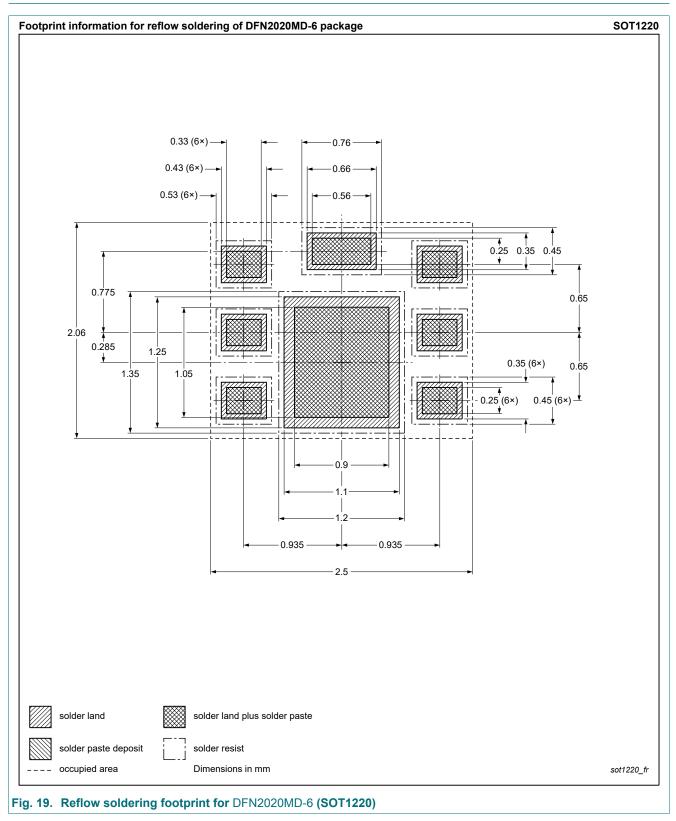
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### 12. Package outline



#### 40 V, N-channel Trench MOSFET

### 13. Soldering



# 14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
BUK6D20-40E v.1	20230925	Product data sheet	-	-		

BUK6D20-40E

## 15. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

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